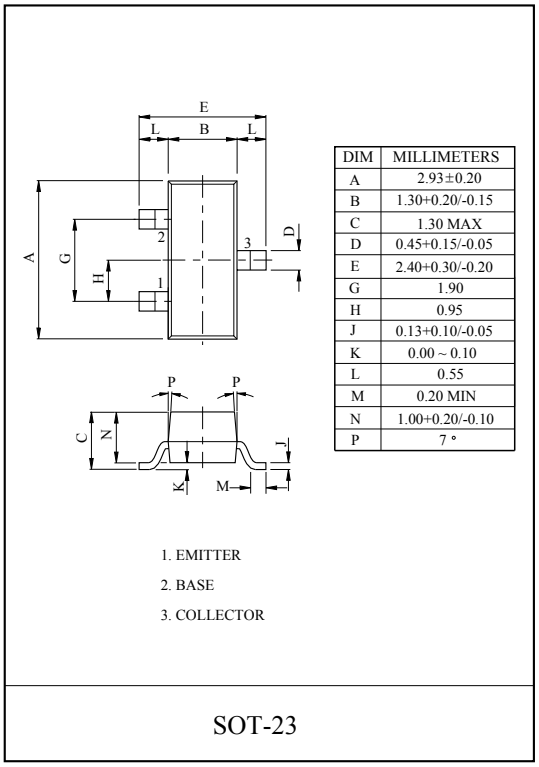
BSS64

EPITAXIAL PLANAR NPN TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.



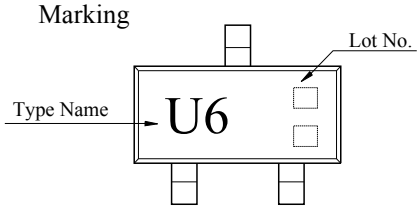
DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/-0.15
C	1.30 MAX
D	0.45+0.15/-0.05
E	2.40+0.30/-0.20
G	1.90
H	0.95
J	0.13+0.10/-0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/-0.10
P	7 °

SOT-23

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Emitter Current	I_E	-100	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-65 ~ 150	℃

Marking



ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=4mA, I_B=0	80	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	120	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5.0	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB}=90V, I_E=0	-	-	100	nA
		V_{CB}=90V, I_E=0, Ta=150℃	-	-	50	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	200	nA
DC Current Gain	h_{FE}	V_{CE}=1V, I_C=1mA	-	60	-	
		V_{CE}=1V, I_C=4mA	20	-	-	
		V_{CE}=1V, I_C=10mA	-	80	-	
		V_{CE}=1V, I_C=20mA	-	55	-	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=4mA, I_B=0.4mA	-	-	1.2	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=4mA, I_B=0.4mA	-	-	0.15	V
		I_C=50mA, I_B=15mA	-	-	0.2	
Transition Frequency	f_T	V_{CE}=10V, I_C=4mA, f=100MHz	60	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz	-	-	5.0	pF

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